

# PSMN8R5-100PSF

NextPower 100 V, 8.7 m $\Omega$  N-channel MOSFET in TO220 package

10 April 2017

**Product data sheet** 

## 1. General description

NextPower 100 V standard level gate drive MOSFET. Qualified to 175 °C and recommended for industrial & consumer applications.

### 2. Features and benefits

- · Optimised for fast switching, low spiking, high efficiency
- Low Q<sub>G</sub> x R<sub>DSon</sub> FOM for high efficiency switching applications
- Low body diode losses (Q<sub>rr</sub>) and fast recovery (t<sub>rr</sub>)
- Strong avalanche energy rating (E<sub>AS</sub>)
- Avalanche rated & 100% tested
- Ha-free & RoHS compliant TO220 package

## 3. Applications

- Synchronous rectification in AC-to-DC and DC-to-DC applications
- Brushed & BLDC motor control
- · UPS & solar inverter
- · LED lighting
- · Battery protection
- Full-bridge & half-bridge applications
- Flyback & resonant topologies

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	100	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	-	98	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	183	W
Tj	junction temperature			-55	-	175	°C
Static chara	acteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 10		-	7.5	8.7	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 100 °C; Fig. 11		-	11.2	13.5	mΩ
Dynamic ch	naracteristics			'			
$Q_{GD}$	gate-drain charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V;		-	8.7	-	nC
Q <sub>G(tot)</sub>	total gate charge	Fig. 12; Fig. 13		-	44.5	-	nC



Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche ruggedness							
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 34 A; $V_{sup}$ ≤ 100 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; Fig. 4; Unclamped	[2]	-	-	281	mJ

- [1] Avalanche current is limited by I<sub>AS</sub>
- [2] Protected by 100% test

## 5. Pinning information

## **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain	<b>├</b>	
3	S	source		G P
mb	D	mounting base; connected to drain	TO-220AB (SOT78)	mbb076 S

## 6. Ordering information

## **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
PSMN8R5-100PSF	TO-220AB	plastic, single-ended package (heatsink mounted, 1 mounting hole); 3 leads; 2.54 mm pitch; 15.6 mm x 10 mm x 4.4 mm body	SOT78			

## 7. Marking

## Table 4. Marking codes

Type number	Marking code
PSMN8R5-100PSF	PSMN8R5-100PSF

## 8. Limiting values

## **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	100	V
$V_{DGR}$	drain-gate voltage	25 °C ≤ $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ		-	100	V
$V_{GS}$	gate-source voltage			-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	183	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	98	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>		-	69	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$ ; Fig. 3		-	391	Α
T <sub>stg</sub>	storage temperature			-55	175	°C
T <sub>j</sub>	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-drai	n diode		'		'	
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	98	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	391	Α
Avalanche r	uggedness			'	,	
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 34 A; $V_{sup} \le 100$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; Fig. 4; Unclamped	[2]	-	281	mJ
I <sub>AS</sub>	non-repetitive avalanche current	$V_{sup} \le 100 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C}; R_{GS} = 50 \Omega$	[2]	-	34	Α

<sup>[1]</sup> Avalanche current is limited by I<sub>AS</sub>

<sup>[2]</sup> Protected by 100% test

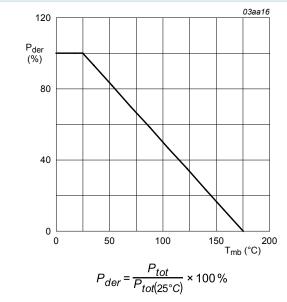


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

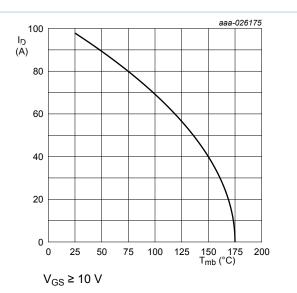
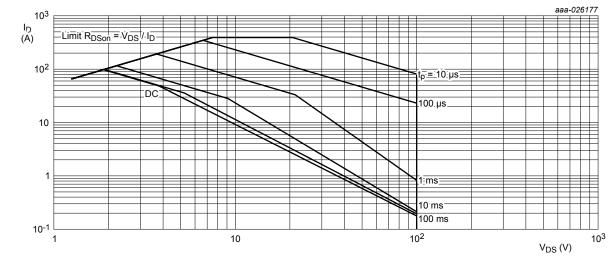
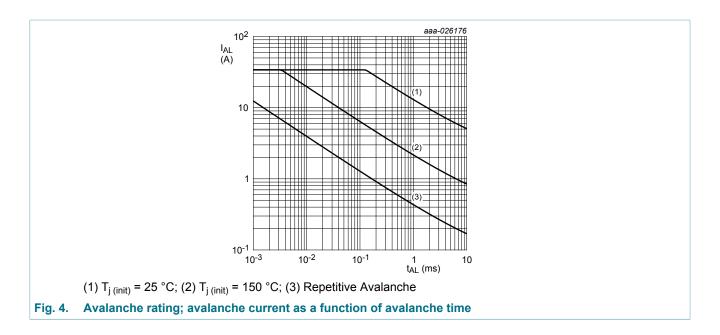


Fig. 2. Continuous drain current as a function of mounting base temperature



T<sub>mb</sub> = 25 °C; I<sub>DM</sub> is a single pulse

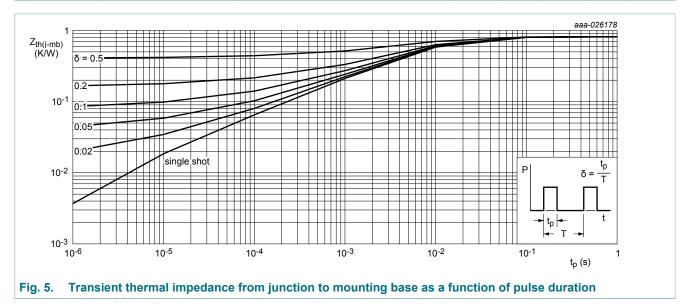
Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	0.71	0.82	K/W



## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	cteristics			'		
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	100	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	90	-	-	V
()	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	3.6	-	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	-	1.8	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 9$	2	3.1	4	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-8.4	-	mV/k
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.05	1	μΑ
		V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	5	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	5	100	nA
$R_{DSon}$	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 10	-	7.5	8.7	mΩ
		V <sub>GS</sub> = 7 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	8.9	13.2	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; Fig. 11	-	11.2	13.5	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 11	-	16	19	mΩ
$R_G$	gate resistance	f = 1 MHz	-	1.54	-	Ω
Dynamic cha	aracteristics					<u> </u>
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; Fig. 12; Fig. 13	-	44.5	-	nC
		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V	-	22.9	-	nC
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V;	-	14.5	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	Fig. 12; Fig. 13	-	8.8	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	5.6	-	nC
$Q_{GD}$	gate-drain charge		-	8.7	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; <u>Fig. 12</u> ; <u>Fig. 13</u>	-	4.8	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	3181	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 14</u>	-	551	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	12	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 2 \Omega; V_{GS} = 10 \text{ V};$	-	16.8	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 ^{\circ}C$	-	26.8	-	ns

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
t <sub>d(off)</sub>	turn-off delay time			-	31.5	-	ns		
t <sub>f</sub>	fall time			-	23.6	-	ns		
Source-drain diode									
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 15$		-	0.83	1.2	V		
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ;		-	51	-	ns		
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 50 V; <u>Fig. 16</u>		-	70	-	nC		

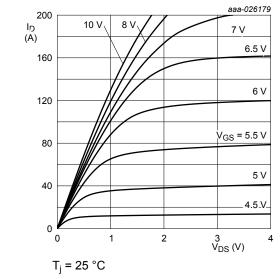


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

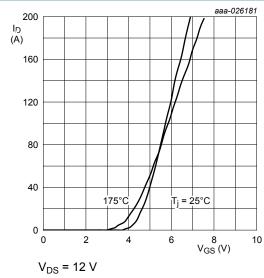


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

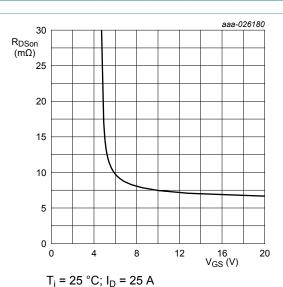


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

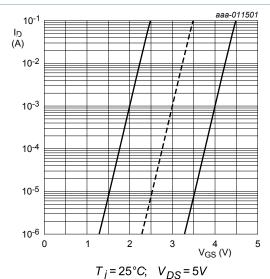


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

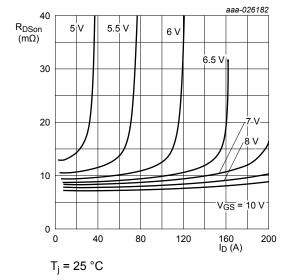


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

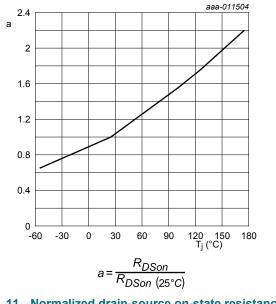


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

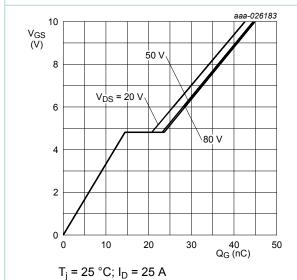


Fig. 12. Gate-source voltage as a function of gate charge; typical values

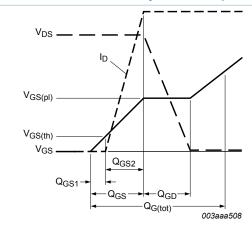


Fig. 13. Gate charge waveform definitions

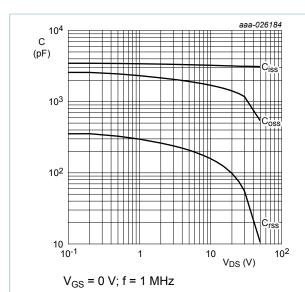
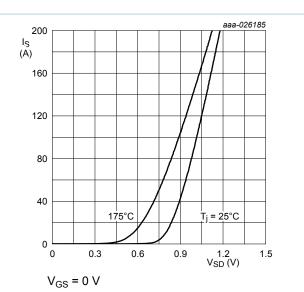


Fig. 14. Input, output and reverse transfer capacitances | Fig. 15. Source-drain (diode forward) current as a as a function of drain-source voltage; typical values



function of source-drain (diode forward) voltage; typical values

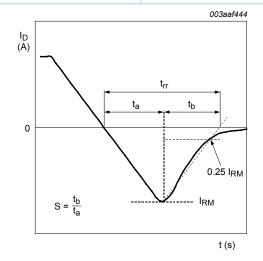
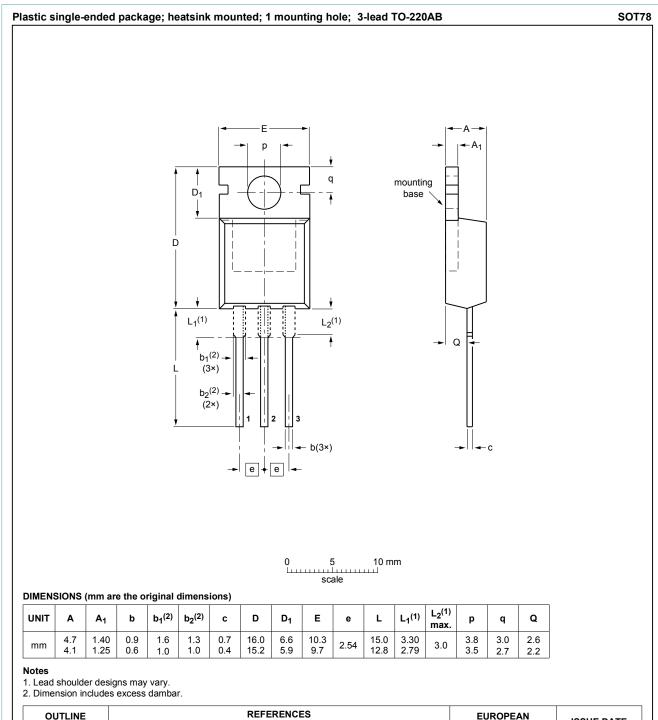


Fig. 16. Reverse recovery timing definition

## 11. Package outline



VERSION IEC JEDEC JEITA PROJECTION ISSUE DATE   SOT78 3-lead TO-220AB SC-46 ISSUE DATE 08-04-23-08-06-13	OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
$1  SO1/8  1  13 \log_2 TO(2200R)  SC-46  1  1  + - \rightarrow H+W$	VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
	SOT78		3-lead TO-220AB	SC-46		

Fig. 17. Package outline TO-220AB (SOT78)

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## 12. Legal information

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Document status [1][2]	Product status [3]	Definition
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